

Vishay General Semiconductor

HALOGEN

FREE

Surface Mount PAR® Transient Voltage Suppressors

High Temperature Stability and High Reliability Conditions



DO-218 Compatible



LINKS TO ADDITIONAL RESOURCES







PRIMARY CHARACTERISTICS					
V _{WM}	10 V to 85 V				
V _{BR}	11.1 V to 104 V				
P _{PPM} (10 x 1000 μs)	6600 W				
P _{PPM} (10 x 10 000 μs)	5200 W				
P_{D}	8 W				
I _{FSM}	700 A				
T _J max.	175 °C				
Polarity	Unidirectional				
Package	DO-218AC				

FEATURES

- Junction passivation optimized design passivated anisotropic rectifier technology
- T_J = 175 °C capability suitable for high reliability and automotive requirement
- Unidirectional
- Low leakage current
- Low forward voltage drop
- High surge capability
- Meets ISO7637-2 surge specification (varied by test condition)
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified available
 - Automotive ordering code: base P/NHM3
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

Use in sensitive electronics protection against voltage transients induced by inductive load switching and lightning, especially for automotive load dump protection application.

MECHANICAL DATA

Case: DO-218AC

Molding compound meets UL 94 V-0 flammability rating Base P/NHM3 - RoHS-compliant, AEC-Q101 qualified

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

HM3 suffix meets JESD 201 class 2 whisker test

Polarity: heatsink is anode

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	VALUE	UNIT			
Dool, and a manner discipation	with 10/1000 µs waveform	В	6600	w		
Peak pulse power dissipation	with 10/10 000 µs waveform	P _{PPM}	5200			
Power dissipation on infinite heats	P _D	8.0	W			
Peak pulse current with 10/1000 µ	I _{PPM} ⁽¹⁾	See next table	Α			
Peak forward surge current 8.3 m	I _{FSM}	700	Α			
Operating junction and storage te	T _J , T _{STG}	-55 to +175	°C			

Note

(1) Non-repetitive current pulse at T_A = 25 °C

SM8S10AHM3 thru SM8S85AHM3

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ELECTRICA	ELECTRICAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)									
DEVICE TYPE	BREAKDOWN VOLTAGE V _{BR} (V)		TEST CURRENT	STAND-OFF VOLTAGE V _{WM}	MAXIMUM REVERSE LEAKAGE	MAXIMUM REVERSE LEAKAGE AT V _{WM}	MAX. PEAK PULSE CURRENT AT 10/1000 µs	MAXIMUM CLAMPING VOLTAGE	TYPICAL TEMP. COEFFICIENT OF V _{BR} ⁽¹⁾	
	MIN.	NOM.	MAX.	I _T (mA)	(V)	AT V _{WM} I _D (μA)	T _J = 175 °C I _D (μA)	WAVEFORM (A)	AT I _{PPM} V _C (V)	αT (%/°C)
SM8S10AHM3	11.1	11.7	12.3	5.0	10.0	15	250	388	17.0	0.069
SM8S11AHM3	12.2	12.9	13.5	5.0	11.0	10	150	363	18.2	0.072
SM8S12AHM3	13.3	14.0	14.7	5.0	12.0	10	150	332	19.9	0.074
SM8S13AHM3	14.4	15.2	15.9	5.0	13.0	10	150	307	21.5	0.076
SM8S14AHM3	15.6	16.4	17.2	5.0	14.0	10	150	284	23.2	0.078
SM8S15AHM3	16.7	17.6	18.5	5.0	15.0	10	150	270	24.4	0.080
SM8S16AHM3	17.8	18.8	19.7	5.0	16.0	10	150	254	26.0	0.081
SM8S17AHM3	18.9	19.9	20.9	5.0	17.0	10	150	239	27.6	0.082
SM8S18AHM3	20.0	21.1	22.1	5.0	18.0	10	150	226	29.2	0.083
SM8S20AHM3	22.2	23.4	24.5	5.0	20.0	10	150	204	32.4	0.085
SM8S22AHM3	24.4	25.7	26.9	5.0	22.0	10	150	186	35.5	0.086
SM8S24AHM3	26.7	28.1	29.5	5.0	24.0	10	150	170	38.9	0.087
SM8S26AHM3	28.9	30.4	31.9	5.0	26.0	10	150	157	42.1	0.088
SM8S28AHM3	31.1	32.8	34.4	5.0	28.0	10	150	145	45.4	0.089
SM8S30AHM3	33.3	35.1	36.8	5.0	30.0	10	150	136	48.4	0.090
SM8S33AHM3	36.7	38.7	40.6	5.0	33.0	10	150	124	53.3	0.091
SM8S36AHM3	40.0	42.1	44.2	5.0	36.0	10	150	114	58.1	0.091
SM8S40AHM3	44.4	46.8	49.1	5.0	40.0	10	150	102	64.5	0.092
SM8S43AHM3	47.8	50.3	52.8	5.0	43.0	10	150	95.1	69.4	0.093
SM8S45AHM3	50.0	52.7	55.3	5.0	45.0	10	150	90.8	72.7	0.093
SM8S48AHM3	53.3	56.1	58.9	5.0	48.0	10	150	85.3	77.4	0.093
SM8S51AHM3	56.7	59.7	62.7	5.0	51.0	10	150	80.1	82.4	0.093
SM8S54AHM3	60.0	63.2	66.3	5.0	54.0	10	150	75.8	87.1	0.093
SM8S58AHM3	64.4	67.8	71.2	5.0	58.0	10	150	70.5	93.6	0.093
SM8S60AHM3	66.7	70.2	73.7	5.0	60.0	10	150	68.2	96.8	0.093
SM8S64AHM3	71.1	74.9	78.6	5.0	64.0	10	150	64.1	103	0.093
SM8S70AHM3	77.8	81.9	86.0	5.0	70.0	10	150	58.4	113	0.093
SM8S75AHM3	83.3	87.7	92.1	5.0	75.0	10	150	54.5	121	0.093
SM8S78AHM3	86.7	91.3	95.8	5.0	78.0	10	150	52.4	126	0.093
SM8S85AHM3	94.4	99.2	104	5.0	85.0	10	150	48.2	137	0.093

Notes

⁽¹⁾ To calculate V_{BR} vs. junction temperature, use the following formula: V_{BR} at T_J = V_{BR} at 25 °C x (1 + αT x (T_J - 25))

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	VALUE	UNIT			
Typical thermal resistance	$R_{\theta JA}$ (1)	55	°C/W			
Typical thermal resistance	R _{0JM} (2)	0.35	°C/W			

Notes

[•] For all types maximum $V_F = 1.8 \text{ V}$ at $I_F = 100 \text{ A}$ measured on 300 μs square pulse width

 $^{^{(1)}}$ Thermal resistance junction-to-ambient to follow JEDEC®51-2A, device mounted on FR4 PCB, 2 oz. standard footprint

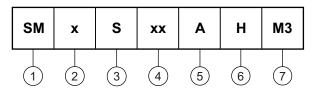
⁽²⁾ Thermal resistance junction-to-mount to follow JEDEC®51-14 using Transient Dual Interface Test Method (TDIM)

SM8S10AHM3 thru SM8S85AHM3

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ORDERING INFORMATION TABLE

Device code



1 - Surface mount

2 - Power dissipation P_D (5 = 5 W, 6 = 6 W, 8 = 8 W)

Standard V_F type

Stand-off voltage

5 - Breakdown voltage tolerance and polarity (A ± 5 %, unidirectional)

- Quality grade (H = AEC-Q101 qualified, otherwise = industry grade)

- Material / Environment category (M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE	
SM8S10AHM3/I ⁽¹⁾	2.605	I	750	13" diameter plastic tape and reel, anode towards the sprocket hole	

Note

(1) AEC-Q101 qualified

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RATINGS AND CHARACTERISTICS CURVES (T_A = 25 °C unless otherwise noted)

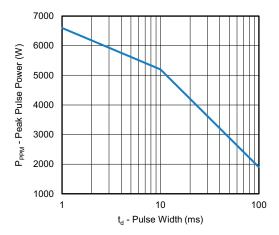


Fig. 1 - Peak Pulse Power Derating Curve

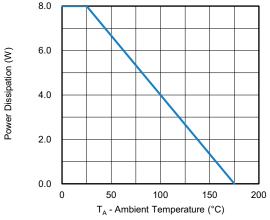


Fig. 2 - Power Derating Curve

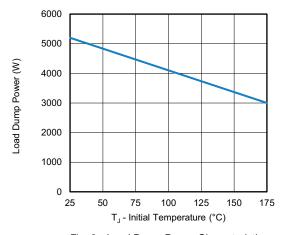


Fig. 3 - Load Dump Power Characteristics (10 ms Exponential Waveform)

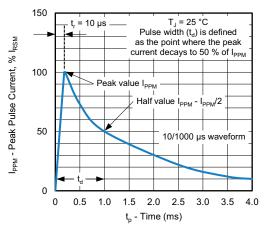


Fig. 4 - Pulse waveform

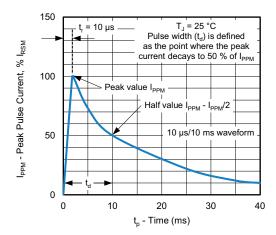


Fig. 5 - Pulse Waveform

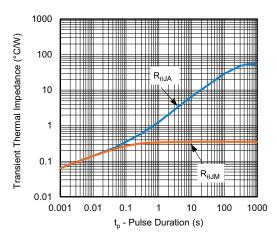


Fig. 6 - Typical Transient Thermal Impedance

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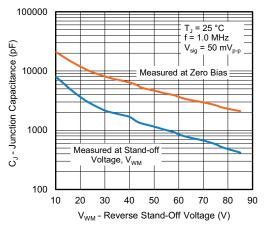
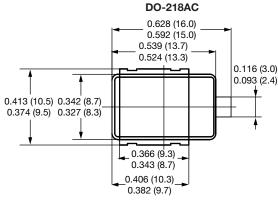
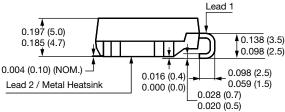


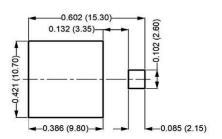
Fig. 7 - Junction Capacitance

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





Mounting Pad Layout



Note

• Footprint in accordance with IPC 7351 standard



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